



IMZ88

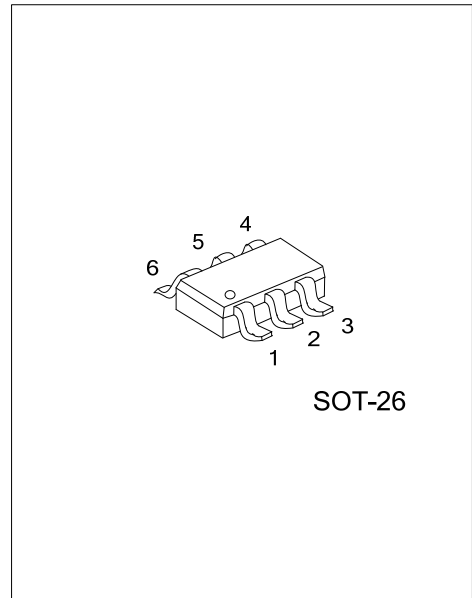
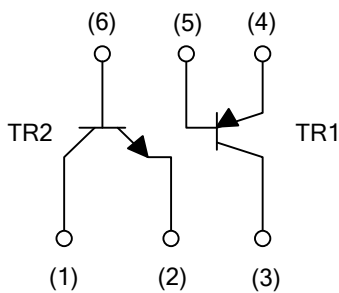
DUAL TRANSISTOR

**GENERAL PURPOSE
(DUAL TRANSISTOR)**

■ **FEATURES**

*Both a 8550S chip and 8050S chip in a SMT package

■ **EQUIVALENT CIRCUITS**

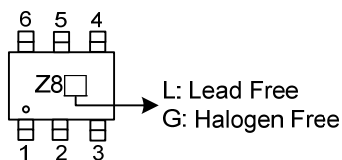


■ **ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
IMZ88L-AG6 -R	IMZ88G-AG6-R	SOT-26	C2	E2	C1	E1	B1	B2	Tape Reel

<p>IMZ88L-AG6-R</p>	<p>(1) R: Tape Reel (2) AG6: SOT-26 (3) G: Halogen Free, L: Lead Free</p>
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■ **MARKING**



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

PARAMETER	SYMBOL	RATING		UNIT
		TR1	TR2	
Collector-Base Voltage	V _{CBO}	-30	30	V
Collector-Emitter Voltage	V _{CEO}	-20	20	V
Emitter-Base Voltage	V _{EBO}	-5	5	V
Collector Current	I _C	-700	700	mA
Power Dissipation (Note 1)	P _D	300		mW
Junction Temperature	T _J	150		°C
Storage Temperature	T _{STG}	-65~+150		°C

Note: 1. 200mW per element must not be exceeded.

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
TR1						
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0	-30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA, I _B =0	-20			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA, I _C =0	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-30V, I _E =0			-1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	μA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-0.5	V
Base-emitter saturation voltage	V _{BE(SAT)}	I _C =500mA, I _B =-50mA			-1.2	V
Base-emitter saturation voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA			-1.0	V
DC Current Transfer Ratio	h _{FE1}	V _{CE} =-1V, I _C =-1mA	100			
	h _{FE2}	V _{CE} =-1V, I _C =-150mA	120	110	400	
	h _{FE3}	V _{CE} =-1V, I _C =-500mA	40			
Transition Frequency	f _T	V _{CE} =-10V, I _C =-50mA	100			MHz
Output Capacitance	C _{OB}	V _{CB} =10V, I _E =0, f=1MHz		9.0		pF
TR2						
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA, I _E =0	30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	20			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =100μA, I _C =0	5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =30V			1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =5V			100	μA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =500mA, I _B =50mA			0.5	V
Base-emitter saturation voltage	V _{BE(SAT)}	I _C =500mA, I _B =50mA			1.2	V
Base-emitter saturation voltage	V _{BE}	V _{CE} =1V, I _C =10mA			1.0	V
DC Current Transfer Ratio	h _{FE1}	V _{CE} =1V, I _C =1mA	100			
	h _{FE2}	V _{CE} =1V, I _C =150mA	120	110	400	
	h _{FE3}	V _{CE} =1V, I _C =500mA	40			
Transition Frequency	f _T	V _{CE} =10V, I _C =50mA	100			MHz
Output Capacitance	C _{OB}	V _{CB} =10V, I _E =0, f=1MHz		9.0		pF

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